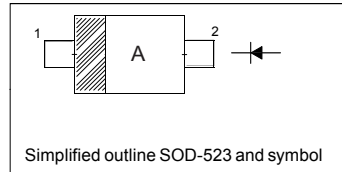


Silicon Epitaxial Planar Switching Diode

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



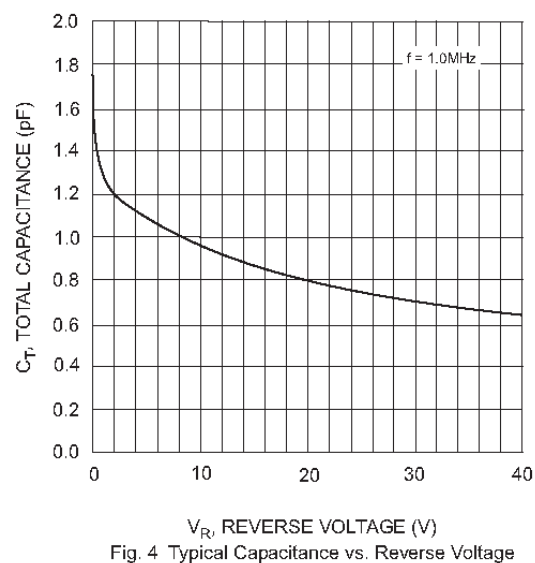
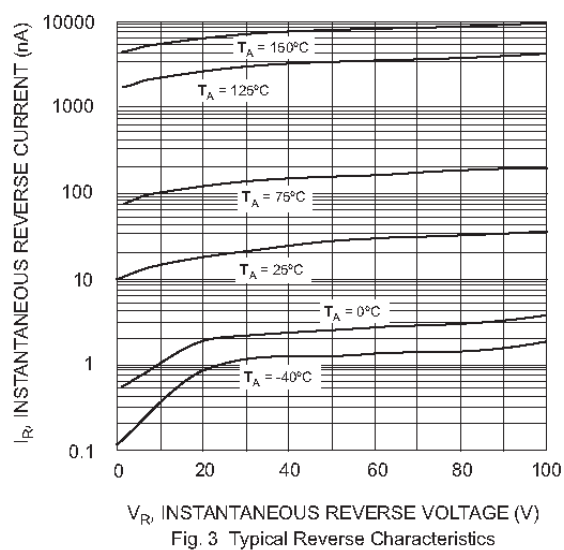
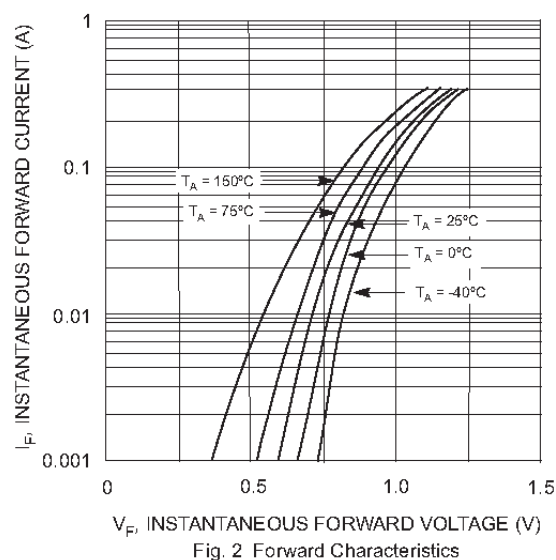
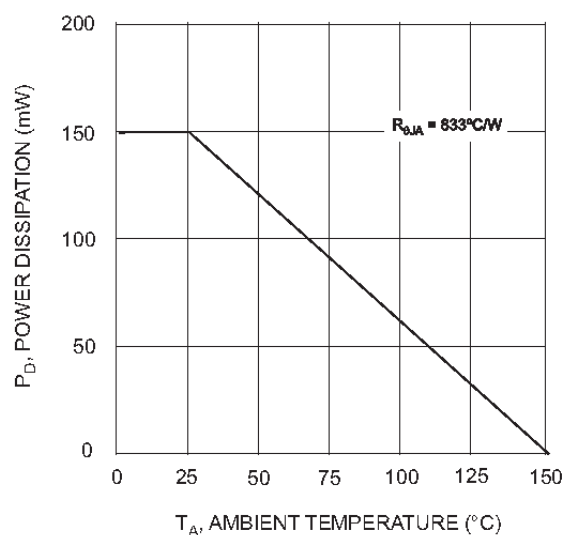
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Symbol	Parameter	Value	Unit
V_{RM}	Non-Repetitive Peak Reverse Voltage	100	V
V_R	Reverse Voltage	75	V
V_{RRM}	Peak Repetitive Reverse Voltage		
V_{RWM}	Working Peak Reverse Voltage		
$V_{R(RMS)}$	RMS Reverse Voltage	53	V
I_O	Average Rectified Output Current	150	mA
I_{FM}	Forward Continuous Current	300	mA
I_{FSM}	Non-repetitive Peak Forward Surge Current @ $t = 8.3\text{ms}$	2	A
P_D	Power Dissipation	150	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	833	$^\circ\text{C/W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

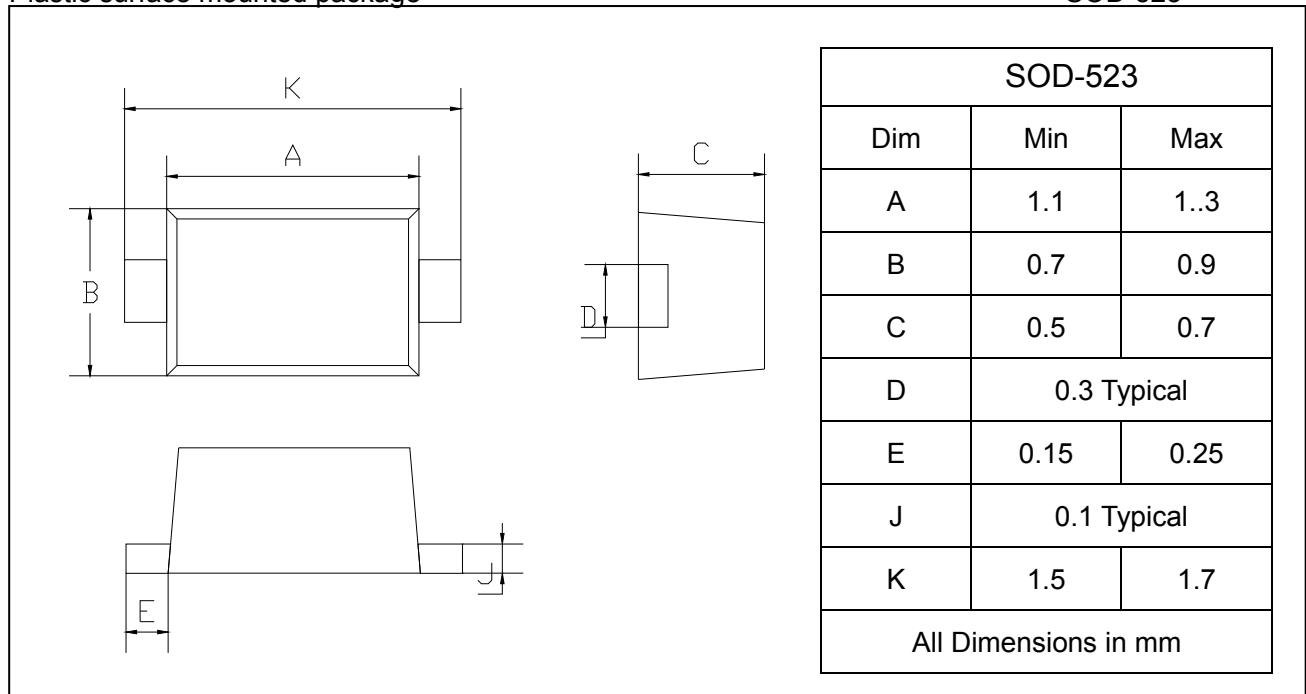
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R = 1\mu\text{A}$	75			V
Reverse current	I_R	$V_R = 75\text{V}$			1	μA
		$V_R = 20\text{V}$			25	nA
Forward voltage	V_F	$I_F = 1\text{mA}$			0.715	V
		$I_F = 10\text{mA}$			0.855	V
		$I_F = 50\text{mA}$			1	V
		$I_F = 150\text{mA}$			1.25	V
Total capacitance	C_{tot}	$V_R = 0\text{V}, f = 1\text{MHz}$			2	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 10\text{mA}, I_{rr} = 0.1 \cdot I_R, R_L = 100\Omega$			4	ns

Typical Characteristics



Plastic surface mounted package

SOD-523



SOLDERING FOOTPRINT

